74AVC1T45

Dual supply translating transceiver; 3-state Rev. 02 — 5 May 2009

Product data sheet

General description

The 74AVC1T45 is a single bit, dual supply transceiver with 3-state output that enables bidirectional level translation. It features one data input-output port (A and B), a direction control input (DIR) and dual supply pins ($V_{CC(A)}$ and $V_{CC(B)}$). Both $V_{CC(A)}$ and $V_{CC(B)}$ can be supplied at any voltage between 0.8 V and 3.6 V making the device suitable for translating between any of the low voltage nodes (0.8 V, 1.2 V, 1.5 V, 1.8 V, 2.5 V and 3.3 V). Pins A and DIR are referenced to V_{CC(A)} and pin B is referenced to V_{CC(B)}. A HIGH on DIR allows transmission from A to B and a LOW on DIR allows transmission from B to Α.

The device is fully specified for partial power-down applications using I_{OFF}. The I_{OFF} circuitry disables the output, preventing any damaging backflow current through the device when it is powered down. In suspend mode when either V_{CC(A)} or V_{CC(B)} are at GND level, both A and B are in the high-impedance OFF-state.

Features 2.

- Wide supply voltage range:
 - ◆ V_{CC(A)}: 0.8 V to 3.6 V
 - ◆ V_{CC(B)}: 0.8 V to 3.6 V
- High noise immunity
- Complies with JEDEC standards:
 - ◆ JESD8-12 (0.8 V to 1.3 V)
 - ◆ JESD8-11 (0.9 V to 1.65 V)
 - ◆ JESD8-7 (1.2 V to 1.95 V)
 - ◆ JESD8-5 (1.8 V to 2.7 V)
 - ◆ JESD8-B (2.7 V to 3.6 V)
- ESD protection:
 - HBM JESD22-A114E Class 3B exceeds 8000 V
 - MM JESD22-A115-A exceeds 200 V
 - CDM JESD22-C101C exceeds 1000 V
- Maximum data rates:
 - ◆ 500 Mbit/s (1.8 V to 3.3 V translation)
 - ◆ 320 Mbit/s (< 1.8 V to 3.3 V translation)
 - 320 Mbit/s (translate to 2.5 V or 1.8 V)
 - 280 Mbit/s (translate to 1.5 V)
 - 240 Mbit/s (translate to 1.2 V)
- Suspend mode
- Latch-up performance exceeds 100 mA per JESD 78 Class II



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- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot < 10 % of V_{CC}
- I_{OFF} circuitry provides partial Power-down mode operation
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C

3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74AVC1T45GW	–40 °C to +125 °C	SC-88	plastic surface-mounted package; 6 leads	SOT363
74AVC1T45GM	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 \times 1.45 \times 0.5 mm	SOT886

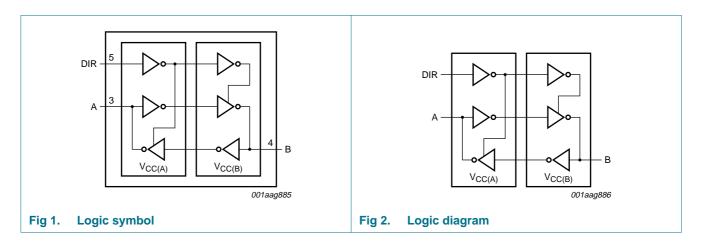
4. Marking

Table 2. Marking

Type number	Marking code ^[1]
74AVC1T45GW	B5
74AVC1T45GM	B5

^[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

5. Functional diagram



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6. Pinning information

6.1 Pinning



6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
$V_{CC(A)}$	1	supply voltage port A and DIR
GND	2	ground (0 V)
A	3	data input or output
В	4	data input or output
DIR	5	direction control
V _{CC(B)}	6	supply voltage port B

7. Functional description

Table 4. Function table[1]

Supply voltage	Input	Input/output ^[2]			
V _{CC(A)} , V _{CC(B)}	DIR[3]	Α	В		
0.8 V to 3.6 V	L	A = B	input		
0.8 V to 3.6 V	Н	input	B = A		
GND[4]	Χ	Z	Z		

- [1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.
- [2] The input circuit of the data I/O is always active.
- [3] The DIR input circuit is referenced to V_{CC(A)}.
- [4] When either $V_{CC(A)}$ or $V_{CC(B)}$ is at GND level, the device goes into suspend mode.

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

			•		•
Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC(A)}$	supply voltage port A		-0.5	+4.6	V
V _{CC(B)}	supply voltage port B		-0.5	+4.6	V
I _{IK}	input clamping current	V _I < 0 V	-50	-	mA
VI	input voltage		<u>[1]</u> –0.5	+4.6	V
lok	output clamping current	V _O < 0 V	-50	-	mA
Vo	output voltage	Active mode	<u>[1][2][3]</u> –0.5	$V_{CCO} + 0.5$	V
		Suspend or 3-state mode	<u>[1]</u> –0.5	+4.6	V
Io	output current	$V_O = 0 V \text{ to } V_{CCO}$	-	±50	mA
I _{CC}	supply current	I _{CC(A)} or I _{CC(B)}	-	100	mA
I _{GND}	ground current		-100	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	T_{amb} = -40 °C to +125 °C	<u>[4]</u> -	250	mW

^[1] The minimum input voltage ratings and output voltage ratings may be exceeded if the input and output current ratings are observed.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC(A)}$	supply voltage A		8.0	3.6	V
$V_{CC(B)}$	supply voltage B		8.0	3.6	V
V_{I}	input voltage		0	3.6	V
Vo	output voltage	Active mode	<u>[1]</u> 0	V_{CCO}	V
		Suspend or 3-state mode	0	3.6	V
T_{amb}	ambient temperature		-40	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CCI} = 0.8 \text{ V to } 3.6 \text{ V}$	[2] -	5	ns/V

^[1] V_{CCO} is the supply voltage associated with the output port.

^[2] V_{CCO} is the supply voltage associated with the output port.

^[3] V_{CCO} + 0.5 V should not exceed 4.6 V.

^[4] For SC-88 packages: above 87.5 °C the value of P_{tot} derates linearly with 4.0 mW/K. For XSON6 package: above 118 °C the value of P_{tot} derates linearly with 7.8 mW/K.

^[2] V_{CCI} is the supply voltage associated with the input port.

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10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T _{amb} = 2	5 °C					
V _{OH}	HIGH-level	$V_I = V_{IH}$ or V_{IL}				
	output voltage	$I_{O} = -1.5 \text{ mA}; V_{CC(A)} = V_{CC(B)} = 0.8 \text{ V}$	-	0.69	-	V
V_{OL}	LOW-level	$V_I = V_{IH}$ or V_{IL}				
	output voltage	$I_O = 1.5 \text{ mA}; V_{CC(A)} = V_{CC(B)} = 0.8 \text{ V}$	-	0.07	-	V
I _I	input leakage current	DIR input; $V_I = 0 \text{ V to } 3.6 \text{ V}$; $V_{CC(A)} = V_{CC(B)} = 0.8 \text{ V to } 3.6 \text{ V}$	-	±0.025	±0.25	μΑ
l _{OZ}	OFF-state output current	A or B port; $V_O = 0 \text{ V or } V_{CCO}$; $V_{CC(A)} = V_{CC(B)} = 0.8 \text{ V to } 3.6 \text{ V}$	<u>[1]</u> -	±0.5	±2.5	μΑ
l _{OFF}	power-off leakage current	A port; V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC(A)} = 0$ V; $V_{CC(B)} = 0.8$ V to 3.6 V	-	±0.1	±1	μΑ
S		B port; V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC(B)} = 0$ V; $V_{CC(A)} = 0.8$ V to 3.6 V	-	±0.1	±1	μΑ
Cı	input capacitance	DIR input; $V_I = 0 \text{ V or } 3.3 \text{ V};$ $V_{CC(A)} = V_{CC(B)} = 3.3 \text{ V}$	-	1	-	pF
C _{I/O}	input/output capacitance	A and B port; suspend mode; $V_O = 3.3 \text{ V or 0 V};$ $V_{CC(A)} = V_{CC(B)} = 3.3 \text{ V}$	-	4	-	pF
T _{amb} = -	40 °C to +85 °C					
V_{IH}	HIGH-level input voltage	data input	[2]			
		V _{CCI} = 0.8 V	0.70V _{CCI}	-	-	V
		V _{CCI} = 1.1 V to 1.95 V	0.65V _{CCI}	-	-	V
		$V_{CCI} = 2.3 \text{ V to } 2.7 \text{ V}$	1.6	-	-	V
		V _{CCI} = 3.0 V to 3.6 V	2	-	-	V
		DIR input				
		$V_{CCI} = 0.8 \text{ V}$	$0.70V_{CC(A)}$	-	-	V
		V _{CCI} = 1.1 V to 1.95 V	0.65V _{CC(A)}	-	-	V
		$V_{CCI} = 2.3 \text{ V to } 2.7 \text{ V}$	1.6	-	-	V
		V _{CCI} = 3.0 V to 3.6 V	2	-	-	V
V_{IL}	LOW-level	data input	[2]			
	input voltage	V _{CCI} = 0.8 V	-	-	0.30V _{CCI}	V
		V _{CCI} = 1.1 V to 1.95 V	-	-	0.35V _{CCI}	V
		V _{CCI} = 2.3 V to 2.7 V	-	-	0.7	V
		V _{CCI} = 3.0 V to 3.6 V	-	-	0.9	V
		DIR input				
		V _{CCI} = 0.8 V	-	-	0.30V _{CC(A)}	V
		V _{CCI} = 1.1 V to 1.95 V	-	-	0.35V _{CC(A)}	V
		V _{CCI} = 2.3 V to 2.7 V	-	-	0.7	V
		V _{CCI} = 3.0 V to 3.6 V	-	-	0.9	V

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Table 7. Static characteristics ...continued
At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{OH}	HIGH-level	$V_I = V_{IH}$ or V_{IL}				
	output voltage	$I_O = -100 \ \mu A;$ $V_{CC(A)} = V_{CC(B)} = 0.8 \ V \ to \ 3.6 \ V$	[1] V _{CCO} – 0.1	-	-	V
		$I_O = -3 \text{ mA}; \ V_{CC(A)} = V_{CC(B)} = 1.1 \ V$	0.85	-	-	V
		$I_O = -6 \text{ mA}; V_{CC(A)} = V_{CC(B)} = 1.4 \text{ V}$	1.05	-	-	V
		$I_O = -8 \text{ mA}; V_{CC(A)} = V_{CC(B)} = 1.65 \text{ V}$	1.2	-	-	V
		$I_O = -9 \text{ mA}; V_{CC(A)} = V_{CC(B)} = 2.3 \text{ V}$	1.75	-	-	V
		$I_O = -12 \text{ mA}; V_{CC(A)} = V_{CC(B)} = 3.0 \text{ V}$	2.3	-	-	V
V_{OL}	LOW-level	$V_I = V_{IH}$ or V_{IL}				
	output voltage	$I_O = 100 \ \mu A;$ $V_{CC(A)} = V_{CC(B)} = 0.8 \ V$ to 3.6 V	-	-	0.1	V
		$I_O = 3 \text{ mA}; V_{CC(A)} = V_{CC(B)} = 1.1 \text{ V}$	-	-	0.25	V
		$I_O = 6 \text{ mA}; V_{CC(A)} = V_{CC(B)} = 1.4 \text{ V}$	-	-	0.35	V
		$I_O = 8 \text{ mA}; V_{CC(A)} = V_{CC(B)} = 1.65 \text{ V}$	-	-	0.45	V
		$I_{O} = 9 \text{ mA}; V_{CC(A)} = V_{CC(B)} = 2.3 \text{ V}$	-	-	0.55	V
		$I_O = 12 \text{ mA}; V_{CC(A)} = V_{CC(B)} = 3.0 \text{ V}$	-	-	0.7	V
lı	input leakage current	DIR input; $V_I = 0 \text{ V to } 3.6 \text{ V}$; $V_{CC(A)} = V_{CC(B)} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	±1	μΑ
l _{OZ}	OFF-state output current	A or B port; $V_O = 0 \text{ V or } V_{CCO}$; $V_{CC(A)} = V_{CC(B)} = 0.8 \text{ V to } 3.6 \text{ V}$	<u>[1]</u> -	-	±5	μΑ
I _{OFF}	power-off leakage current	A port; V_I or $V_O = 0$ V to 3.6 V; $V_{CC(A)} = 0$ V; $V_{CC(B)} = 0.8$ V to 3.6 V	-	-	±5	μΑ
		B port; V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC(B)} = 0$ V; $V_{CC(A)} = 0.8$ V to 3.6 V	-	-	±5	μΑ
I _{CC}	supply current	A port; $V_I = 0 \text{ V or } V_{CCI}$; $I_O = 0 \text{ A}$	[2]			
		$V_{CC(A)} = 0.8 \text{ V to } 3.6 \text{ V};$ $V_{CC(B)} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	8.0	μΑ
		$V_{CC(A)} = 3.6 \text{ V}; V_{CC(B)} = 0 \text{ V}$	-	-	8.0	μΑ
		$V_{CC(A)} = 0 \text{ V}; V_{CC(B)} = 3.6 \text{ V}$	-2	0	-	μΑ
		B port; $V_I = 0 \text{ V or } V_{CCI}$; $I_O = 0 \text{ A}$	[2]			
		$V_{CC(A)} = 0.8 \text{ V to } 3.6 \text{ V};$ $V_{CC(B)} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	8.0	μΑ
		$V_{CC(A)} = 3.6 \text{ V}; V_{CC(B)} = 0 \text{ V}$	-2	0	-	μΑ
		$V_{CC(A)} = 0 \text{ V}; V_{CC(B)} = 3.6 \text{ V}$	-	-	8.0	μΑ
		A plus B port ($I_{CC(A)} + I_{CC(B)}$); $I_O = 0$ A; $V_I = GND$ or V_{CCI} ; $V_{CC(A)} = 0.8$ V to 3.6 V; $V_{CC(B)} = 0.8$ V to 3.6 V	[2] -	-	16	μΑ

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Table 7. Static characteristics ...continued
At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T _{amb} = -	40 °C to +125 °C					
V_{IH}	HIGH-level	data input	[2]			
	input voltage	$V_{CCI} = 0.8 \text{ V}$	$0.70V_{\rm CCI}$	-	-	V
		$V_{CCI} = 1.1 \text{ V to } 1.95 \text{ V}$	0.65V _{CCI}	-	-	V
		$V_{CCI} = 2.3 \text{ V to } 2.7 \text{ V}$	1.6	-	-	V
		V _{CCI} = 3.0 V to 3.6 V	2	-	-	V
		DIR input				
		V _{CCI} = 0.8 V	0.70V _{CC(A}) -	-	V
		V _{CCI} = 1.1 V to 1.95 V	0.65V _{CC(A}) -	-	V
		$V_{CCI} = 2.3 \text{ V to } 2.7 \text{ V}$	1.6	-	-	V
		V _{CCI} = 3.0 V to 3.6 V	2	-	-	V
/ _{IL}	LOW-level	data input	<u>[2]</u>			
	input voltage	V _{CCI} = 0.8 V	-	-	$0.30V_{CCI}$	V
		V _{CCI} = 1.1 V to 1.95 V	-	-	$0.35V_{CCI}$	V
		V _{CCI} = 2.3 V to 2.7 V	-	-	0.7	V
		V _{CCI} = 3.0 V to 3.6 V	-	-	0.9	V
		DIR input				
		V _{CCI} = 0.8 V	-	-	0.30V _{CC(A)}	V
		V _{CCI} = 1.1 V to 1.95 V	-	-	0.35V _{CC(A)}	V
		V _{CCI} = 2.3 V to 2.7 V	-	-	0.7	V
		V _{CCI} = 3.0 V to 3.6 V	-	-	0.9	V
/ _{OH}	HIGH-level	$V_I = V_{IH}$ or V_{IL}				
	output voltage	$I_{O} = -100 \ \mu A;$ $V_{CC(A)} = V_{CC(B)} = 0.8 \ V \ to \ 3.6 \ V$	[1] $V_{CCO} - 0.7$	1 -	-	V
		$I_{O} = -3 \text{ mA}; V_{CC(A)} = V_{CC(B)} = 1.1 \text{ V}$	0.85	-	-	V
		$I_{O} = -6 \text{ mA}; V_{CC(A)} = V_{CC(B)} = 1.4 \text{ V}$	1.05	-	-	V
		$I_{O} = -8 \text{ mA}; V_{CC(A)} = V_{CC(B)} = 1.65 \text{ V}$	1.2	-	-	V
		$I_{O} = -9 \text{ mA}; V_{CC(A)} = V_{CC(B)} = 2.3 \text{ V}$	1.75	-	-	V
		$I_{O} = -12 \text{ mA}; V_{CC(A)} = V_{CC(B)} = 3.0 \text{ V}$	2.3	-	-	V
OL.	LOW-level	$V_I = V_{IH}$ or V_{IL}				
	output voltage	$I_O = 100 \ \mu A;$ $V_{CC(A)} = V_{CC(B)} = 0.8 \ V \text{ to } 3.6 \ V$	-	-	0.1	V
		$I_{O} = 3 \text{ mA}; V_{CC(A)} = V_{CC(B)} = 1.1 \text{ V}$	-	-	0.25	V
		$I_O = 6 \text{ mA}; V_{CC(A)} = V_{CC(B)} = 1.4 \text{ V}$	-	-	0.35	V
		$I_O = 8 \text{ mA}; V_{CC(A)} = V_{CC(B)} = 1.65 \text{ V}$	-	-	0.45	V
		$I_O = 9 \text{ mA}; V_{CC(A)} = V_{CC(B)} = 2.3 \text{ V}$	-	-	0.55	V
		$I_O = 12 \text{ mA}; V_{CC(A)} = V_{CC(B)} = 3.0 \text{ V}$	-	-	0.7	V
I	input leakage current	DIR input; $V_I = 0 \text{ V to } 3.6 \text{ V};$ $V_{CC(A)} = V_{CC(B)} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	±1.5	μΑ
OZ	OFF-state output current	A or B port; $V_O = 0 \text{ V or } V_{CCO}$; $V_{CC(A)} = V_{CC(B)} = 0.8 \text{ V to } 3.6 \text{ V}$	[1] -	-	±7.5	μΑ

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 Table 7.
 Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
l _{OFF}	power-off leakage current	A port; V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC(B)} = 0$ V; $V_{CC(A)} = 0.8$ V to 3.6 V	-	-	±35	μΑ
		B port; V_I or V_O = 0 V to 3.6 V; $V_{CC(B)}$ = 0 V; $V_{CC(A)}$ = 0.8 V to 3.6 V	-	-	±35	μΑ
I _{CC}	supply current	A port; $V_I = 0 \text{ V or } V_{CCI}$; $I_O = 0 \text{ A}$	<u>[2]</u>			
	,	$V_{CC(A)} = 0.8 \text{ V to } 3.6 \text{ V};$ $V_{CC(B)} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	12	μΑ
		$V_{CC(A)} = 3.6 \text{ V}; V_{CC(B)} = 0 \text{ V}$	-	-	12	μΑ
		$V_{CC(A)} = 0 \text{ V}; V_{CC(B)} = 3.6 \text{ V}$	-8	0	-	μΑ
		B port; $V_I = 0 \text{ V or } V_{CCI}$; $I_O = 0 \text{ A}$	[2]			
		$V_{CC(A)} = 0.8 \text{ V to } 3.6 \text{ V};$ $V_{CC(B)} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	12	μΑ
		$V_{CC(A)} = 3.6 \text{ V}; V_{CC(B)} = 0 \text{ V}$	-8	0	-	μΑ
		$V_{CC(A)} = 0 \text{ V}; V_{CC(B)} = 3.6 \text{ V}$	-	-	12	μΑ
		A plus B port ($I_{CC(A)} + I_{CC(B)}$); $I_O = 0$ A; $V_I = GND$ or V_{CCI} ; $V_{CC(A)} = 0.8$ V to 3.6 V; $V_{CC(B)} = 0.8$ V to 3.6 V	[2] -	-	24	μΑ

^[1] V_{CCO} is the supply voltage associated with the output port.

^[2] V_{CCI} is the supply voltage associated with the data input port.

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11. Dynamic characteristics

Typical dynamic characteristics at $V_{CC(A)} = 0.8 \text{ V}$ and $T_{amb} = 25 \,^{\circ}\text{C}$ [1] Table 8.

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 7; for wave forms see Figure 5 and Figure 6

		· · · · · · · · · · · · · · · · · · ·							
Symbol	Parameter	Conditions	V _{CC(B)}						Unit
			0.8 V	1.2 V	1.5 V	1.8 V	2.5 V	3.3 V	
t_{pd}	propagation delay	A to B	15.5	8.1	7.6	7.7	8.4	9.2	ns
		B to A	15.5	12.7	12.3	12.2	12.0	11.8	ns
t _{dis}	disable time	DIR to A	12.2	12.2	12.2	12.2	12.2	12.2	ns
		DIR to B	11.7	7.9	7.6	8.2	8.7	10.2	ns
t _{en}	ten enable time	DIR to A	27.2	20.6	19.9	20.4	20.7	22.0	ns
		DIR to B	27.7	20.3	19.8	19.9	20.6	21.4	ns

^[1] t_{pd} is the same as t_{PLH} and t_{PHL}; t_{dis} is the same as t_{PLZ} and t_{PHZ}; t_{en} is the same as t_{PZL} and t_{PZH}. ten is a calculated value using the formula shown in Section 13.4 "Enable times"

Table 9. Typical dynamic characteristics at $V_{CC(B)} = 0.8 \text{ V}$ and $T_{amb} = 25 \,^{\circ}\text{C}$ [1]

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 7; for wave forms see Figure 5 and Figure 6

Symbol	Parameter	Conditions	V _{CC(A)}						Unit
			0.8 V	1.2 V	1.5 V	1.8 V	2.5 V	3.3 V	
t _{pd}	propagation delay	A to B	15.5	12.7	12.3	12.2	12.0	11.8	ns
	B to A	15.5	8.1	7.6	7.7	8.4	9.2	ns	
t _{dis}	disable time	DIR to A	12.2	4.9	3.8	3.7	2.8	3.4	ns
		DIR to B	11.7	9.2	9.0	8.8	8.7	8.6	ns
t _{en} enable time	enable time	DIR to A	27.2	17.3	16.6	16.5	17.1	17.8	ns
	DIR to B	27.7	17.6	16.1	15.9	14.8	15.2	ns	

^[1] t_{pd} is the same as t_{PLH} and t_{PHL} ; t_{dis} is the same as t_{PLZ} and t_{PHZ} ; t_{en} is the same as t_{PZL} and t_{PZH} . ten is a calculated value using the formula shown in Section 13.4 "Enable times"

Table 10. Typical power dissipation capacitance at $V_{CC(A)} = V_{CC(B)}$ and $T_{amb} = 25 \, ^{\circ}C \, \frac{[1][2]}{C}$

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions V _{CC(A)} and V _{CC(B)}							Unit
			0.8 V	1.2 V	1.5 V	1.8 V	2.5 V	3.3 V	
C_{PD}	C _{PD} power dissipation capacitance	A port: (direction A to B); B port: (direction B to A)	1	2	2	2	2	2	pF
		A port: (direction B to A); B port: (direction A to B)	9	11	11	12	14	17	pF

^[1] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma (C_L \times V_{CC}^2 \times f_o)$ where:

 f_i = input frequency in MHz;

fo = output frequency in MHz;

C_L = load capacitance in pF;

V_{CC} = supply voltage in V;

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N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

[2] f_i = 10 MHz; V_I = GND to V_{CC} ; t_r = t_f = 1 ns; C_L = 0 pF; R_L = ∞ Ω .

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Dual supply translating transceiver; 3-state

Table 11. Dynamic characteristics for temperature range -40 °C to +85 °C [1] Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 7; for wave forms see Figure 5 and Figure 6.

Symbol	Parameter	Conditions	V _{CC(B)}								Unit		
			1.2 V ± 0.1 V		1.5 V :	± 0.1 V	1.8 V ±	0.15 V	2.5 V	± 0.2 V	3.3 V	± 0.3 V	'
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
V _{CC(A)} =	1.1 V to 1.3 V												
t _{pd}	propagation	A to B	1.0	9.0	0.7	6.8	0.6	6.1	0.5	5.7	0.5	6.1	ns
	delay	B to A	1.0	9.0	8.0	8.0	0.7	7.7	0.6	7.2	0.5	7.1	ns
t _{dis}	disable time	DIR to A	2.2	8.8	2.2	8.8	2.2	8.8	2.2	8.8	2.2	8.8	ns
		DIR to B	2.2	8.4	1.8	6.7	2.0	6.9	1.7	6.2	2.4	7.2	ns
t _{en}	enable time	DIR to A	-	17.4	-	14.7	-	14.6	-	13.4	-	14.3	ns
		DIR to B	-	17.8	-	15.6	-	14.9	-	14.5	-	14.9	ns
V _{CC(A)} =	1.4 V to 1.6 V												
t _{pd}	propagation	A to B	1.0	8.0	0.7	5.4	0.6	4.6	0.5	3.7	0.5	3.5	ns
	delay	B to A	1.0	6.8	8.0	5.4	0.7	5.1	0.6	4.7	0.5	4.5	ns
t _{dis}	disable time	DIR to A	1.6	6.3	1.6	6.3	1.6	6.3	1.6	6.3	1.6	6.3	ns
		DIR to B	2.0	7.6	1.8	5.9	1.6	6.0	1.2	4.8	1.7	5.5	ns
t _{en}	enable time	DIR to A	-	14.4	-	11.3	-	11.1	-	9.5	-	10.0	ns
		DIR to B	-	14.3	-	11.7	-	10.9	-	10.0	-	9.8	ns
V _{CC(A)} =	1.65 V to 1.95	V											
t _{pd} propagation	A to B	1.0	7.7	0.6	5.1	0.5	4.3	0.5	3.4	0.5	3.1	ns	
	delay	B to A	1.0	6.1	0.7	4.6	0.5	4.4	0.5	3.9	0.5	3.7	ns
t _{dis}	disable time	DIR to A	1.6	5.5	1.6	5.5	1.6	5.5	1.6	5.5	1.6	5.5	ns
		DIR to B	1.8	7.7	1.8	5.7	1.4	5.8	1.0	4.5	1.5	5.2	ns
t _{en}	enable time	DIR to A	-	13.8	-	10.3	-	10.2	-	8.4	-	8.9	ns
		DIR to B	-	13.2	-	10.6	-	9.8	-	8.9	-	8.6	ns
$V_{CC(A)} =$	2.3 V to 2.7 V												
t _{pd}	propagation	A to B	1.0	7.2	0.5	4.7	0.5	3.9	0.5	3.0	0.5	2.6	ns
	delay	B to A	1.0	5.7	0.6	3.8	0.5	3.4	0.5	3.0	0.5	2.8	ns
t _{dis}	disable time	DIR to A	1.5	4.2	1.5	4.2	1.5	4.2	1.5	4.2	1.5	4.2	ns
		DIR to B	1.7	7.3	2.0	5.2	1.5	5.1	0.6	4.2	1.1	4.8	ns
t _{en}	enable time	DIR to A	-	13.0	-	9.0	-	8.5	-	7.2	-	7.6	ns
		DIR to B	-	11.4	-	8.9	-	8.1	-	7.2	-	6.8	ns
$V_{CC(A)} =$	3.0 V to 3.6 V												
t_{pd}	propagation	A to B	1.0	7.1	0.5	4.5	0.5	3.7	0.5	2.8	0.5	2.4	ns
	delay	B to A	1.0	6.1	0.6	3.6	0.5	3.1	0.5	2.6	0.5	2.4	ns
t _{dis}	disable time	DIR to A	1.5	4.7	1.5	4.7	1.5	4.7	1.5	4.7	1.5	4.7	ns
		DIR to B	1.7	7.2	0.7	5.5	0.6	5.5	0.7	4.1	1.7	4.7	ns
t _{en}	enable time	DIR to A	-	13.3	-	9.1	-	8.6	-	6.7	-	7.1	ns
		DIR to B	-	11.8	-	9.2	-	8.4	-	7.5	-	7.1	ns

^[1] t_{pd} is the same as t_{PLH} and t_{PHL} ; t_{dis} is the same as t_{PLZ} and t_{PHZ} ; t_{en} is the same as t_{PZL} and t_{PZH} .

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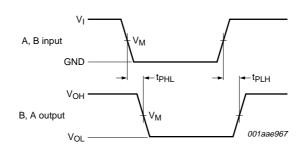
Table 12. Dynamic characteristics for temperature range –40 °C to +125 °C 11 Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 7; for wave forms see Figure 5 and Figure 6

Symbol	Parameter	Conditions	V _{CC(B)}								Unit		
			1.2 V ± 0.1 V		1.5 V	± 0.1 V	1.8 V ±	0.15 V	2.5 V	± 0.2 V	3.3 V	0.3 V	
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
V _{CC(A)} =	1.1 V to 1.3 V												
t _{pd}	propagation	A to B	1.0	9.9	0.7	7.5	0.6	6.8	0.5	6.3	0.5	6.8	ns
	delay	B to A	1.0	9.9	8.0	8.8	0.7	8.5	0.6	8.0	0.5	7.9	ns
t _{dis}	disable time	DIR to A	2.2	9.7	2.2	9.7	2.2	9.7	2.2	9.7	2.2	9.7	ns
	DIR to B	2.2	9.2	1.8	7.4	2.0	7.6	1.7	6.9	2.4	8.0	ns	
t _{en}	enable time	DIR to A	-	19.1	-	16.2	-	16.1	-	14.9	-	15.9	ns
		DIR to B	-	19.6	-	17.2	-	16.5	-	16.0	-	16.5	ns
V _{CC(A)} =	1.4 V to 1.6 V												
t _{pd}	propagation	A to B	1.0	8.8	0.7	6.0	0.6	5.1	0.5	4.1	0.5	3.9	ns
	delay	B to A	1.0	7.5	8.0	6.0	0.7	5.7	0.6	5.2	0.5	5.0	ns
t _{dis} disable tin	disable time	DIR to A	1.6	7.0	1.6	7.0	1.6	7.0	1.6	7.0	1.6	7.0	ns
		DIR to B	2.0	8.3	1.8	6.5	1.6	6.6	1.2	5.3	1.7	6.1	ns
t _{en} enable time	DIR to A	-	15.8	-	12.5	-	12.3	-	10.5	-	11.1	ns	
		DIR to B	-	15.8	-	13.0	-	12.1	-	11.1	-	10.9	ns
V _{CC(A)} =	1.65 V to 1.95	V											
t _{pd} propagation		A to B	1.0	8.5	0.6	5.7	0.5	4.8	0.5	3.8	0.5	3.5	ns
	delay	B to A	1.0	6.8	0.7	5.1	0.5	4.9	0.5	4.3	0.5	4.1	ns
t _{dis}	disable time	DIR to A	1.6	6.1	1.6	6.1	1.6	6.1	1.6	6.1	1.6	6.1	ns
		DIR to B	1.8	8.5	1.8	6.3	1.4	6.4	1.0	5.0	1.5	5.8	ns
t _{en}	enable time	DIR to A	-	15.3	-	11.4	-	11.3	-	9.3	-	9.9	ns
		DIR to B	-	14.6	-	11.8	-	10.9	-	9.9	-	9.6	ns
$V_{CC(A)} =$	2.3 V to 2.7 V												
t_{pd}	propagation	A to B	1.0	8.0	0.5	5.2	0.5	4.3	0.5	3.3	0.5	2.9	ns
	delay	B to A	1.0	6.3	0.6	4.2	0.5	3.8	0.5	3.3	0.5	3.1	ns
t _{dis}	disable time	DIR to A	1.5	4.7	1.5	4.7	1.5	4.7	1.5	4.7	1.5	4.7	ns
		DIR to B	1.7	8.0	2.0	5.8	1.5	5.7	0.6	4.7	1.1	5.3	ns
t _{en}	enable time	DIR to A	-	14.3	-	10.0	-	9.5	-	8.0	-	8.4	ns
		DIR to B	-	12.7	-	9.9	-	9.0	-	8.0	-	7.6	ns
$V_{CC(A)} =$	3.0 V to 3.6 V												
t_{pd}	propagation	A to B	1.0	7.9	0.5	5.0	0.5	4.1	0.5	3.1	0.5	2.7	ns
	delay	B to A	1.0	6.8	0.6	4.0	0.5	3.5	0.5	2.9	0.5	2.7	ns
t_{dis}	disable time	DIR to A	1.5	5.2	1.5	5.2	1.5	5.2	1.5	5.2	1.5	5.2	ns
		DIR to B	1.7	7.9	0.7	6.1	0.6	6.1	0.7	4.6	1.7	5.2	ns
t _{en}	enable time	DIR to A	-	14.7	-	10.1	-	9.6	-	7.5	-	7.9	ns
		DIR to B	-	13.1	-	10.2	-	9.3	-	8.3	-	7.9	ns

^[1] t_{pd} is the same as t_{PLH} and t_{PHL} ; t_{dis} is the same as t_{PLZ} and t_{PHZ} ; t_{en} is the same as t_{PZL} and t_{PZH} .

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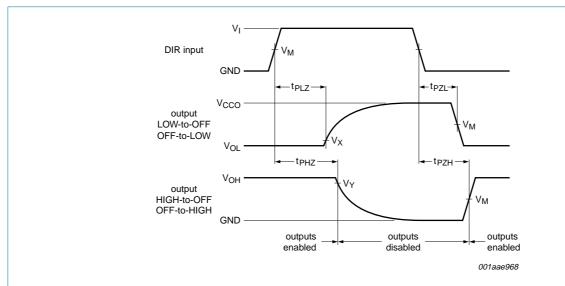
12. Waveforms



Measurement points are given in Table 13.

 $\ensuremath{V_{OL}}$ and $\ensuremath{V_{OH}}$ are typical output voltage drops that occur with the output load.

Fig 5. The data input (A, B) to output (B, A) propagation delay times



Measurement points are given in Table 13.

V_{OL} and V_{OH} are typical output voltage drops that occur with the output load.

Fig 6. Enable and disable times

Table 13. Measurement points

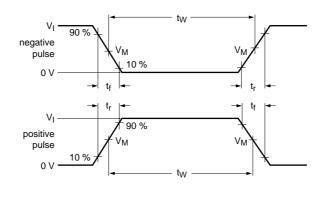
Supply voltage	Input ^[1]	Output ^[2]		
V _{CC(A)} , V _{CC(B)}	V _M	V _M	V _X	V _Y
1.1 V to 1.6 V	0.5V _{CCI}	0.5V _{CCO}	V _{OL} + 0.1 V	V _{OH} – 0.1 V
1.65 V to 2.7 V	0.5V _{CCI}	0.5V _{CCO}	V _{OL} + 0.15 V	$V_{OH} - 0.15 V$
3.0 V to 3.6 V	0.5V _{CCI}	0.5V _{CCO}	V _{OL} + 0.3 V	$V_{OH} - 0.3 V$

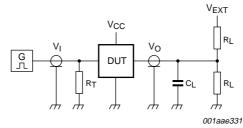
^[1] V_{CCI} is the supply voltage associated with the data input port.

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^[2] V_{CCO} is the supply voltage associated with the output port.

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Test data is given in Table 14.

 R_L = Load resistance.

 C_L = Load capacitance including jig and probe capacitance.

 R_T = Termination resistance.

 V_{EXT} = External voltage for measuring switching times.

Fig 7. Load circuitry for switching times

Table 14. Test data

Supply voltage Input		Load		V _{EXT}	V _{EXT}			
V _{CC(A)} , V _{CC(B)}	V _I [1]	∆t/∆V[2]	CL	R _L	t _{PLH} , t _{PHL}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ} [3]	
1.1 V to 1.6 V	V_{CCI}	≤ 1.0 ns/V	15 pF	2 kΩ	open	GND	2V _{CCO}	
1.65 V to 2.7 V	V_{CCI}	≤ 1.0 ns/V	15 pF	2 kΩ	open	GND	2V _{CCO}	
3.0 V to 3.6 V	V_{CCI}	≤ 1.0 ns/V	15 pF	2 kΩ	open	GND	2V _{CCO}	

[1] V_{CCI} is the supply voltage associated with the data input port.

[2] dV/dt ≥ 1.0 V/ns

[3] V_{CCO} is the supply voltage associated with the output port.

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13. Application information

13.1 Unidirectional logic level-shifting application

The circuit given in <u>Figure 8</u> is an example of the 74AVC1T45 being used in an unidirectional logic level-shifting application.

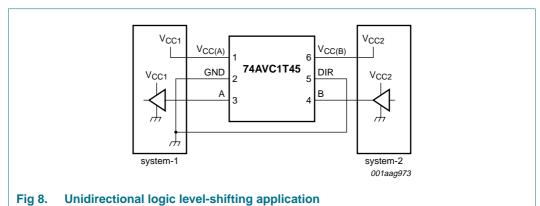


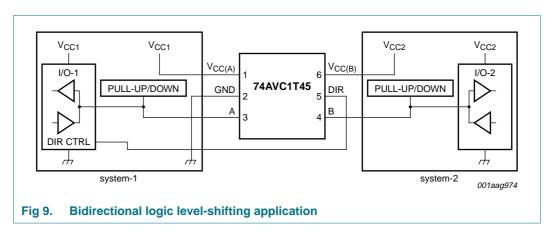
Table 15. Description unidirectional logic level-shifting application

Pin	Name	Function	Description
1	$V_{CC(A)}$	V_{CC1}	supply voltage of system-1 (0.8 V to 3.6 V)
2	GND	GND	device GND
3	Α	OUT	output level depends on V _{CC1} voltage
4	DIR	DIR	the GND (LOW level) determines B port to A port direction
5	В	IN	input threshold value depends on V _{CC2} voltage
6	$V_{CC(B)}$	V_{CC2}	supply voltage of system-2 (0.8 V to 3.6 V)

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13.2 Bidirectional logic level-shifting application

<u>Figure 9</u> shows the 74AVC1T45 being used in a bidirectional logic level-shifting application. Since the device does not have an output enable pin, the system designer should take precautions to avoid bus contention between system-1 and system-2 when changing directions.



<u>Table 16</u> gives a sequence that will illustrate data transmission from system-1 to system-2 and then from system-2 to system-1.

Table 16. Description bidirectional logic level-shifting application[1]

State	DIR CTRL	I/O-1	I/O-2	Description
1	Н	output	input	system-1 data to system-2
2	Н	Z	Z	system-2 is getting ready to send data to system-1. I/O-1 and I/O-2 are disabled. The bus-line state depends on bus hold.
3	L	Z	Z	DIR bit is set LOW. I/O-1 and I/O-2 still are disabled. The bus-line state depends on bus hold.
4	L	input	output	system-2 data to system-1

^[1] H = HIGH voltage level;

L = LOW voltage level;

Z = high-impedance OFF-state.

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13.3 Power-up considerations

The device is designed such that no special power-up sequence is required other than GND being applied first.

Table 17. Typical total supply current $(I_{CC(A)} + I_{CC(B)})$

					-(-)-					
V _{CC(A)}	V _{CC(B)}	V _{CC(B)}								
	0 V	0.8 V	1.2 V	1.5 V	1.8 V	2.5 V	3.3 V			
0 V	0	0.1	0.1	0.1	0.1	0.1	0.1	μΑ		
V 8.0	0.1	0.1	0.1	0.1	0.1	0.7	2.3	μΑ		
1.2 V	0.1	0.1	0.1	0.1	0.1	0.3	1.4	μΑ		
1.5 V	0.1	0.1	0.1	0.1	0.1	0.1	0.9	μΑ		
1.8 V	0.1	0.1	0.1	0.1	0.1	0.1	0.5	μΑ		
2.5 V	0.1	0.7	0.3	0.1	0.1	0.1	0.1	μΑ		
3.3 V	0.1	2.3	1.4	0.9	0.5	0.1	0.1	μΑ		

13.4 Enable times

Calculate the enable times for the 74AVC1T45 using the following formulas:

- t_{en} (DIR to A) = t_{dis} (DIR to B) + t_{pd} (B to A)
- t_{en} (DIR to B) = t_{dis} (DIR to A) + t_{pd} (A to B)

In a bidirectional application, these enable times provide the maximum delay from the time the DIR bit is switched until an output is expected. For example, if the 74AVC1T45 initially is transmitting from A to B, then the DIR bit is switched, the B port of the device must be disabled before presenting it with an input. After the B port has been disabled, an input signal applied to it appears on the corresponding A port after the specified propagation delay.

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14. Package outline

Plastic surface-mounted package; 6 leads

SOT363

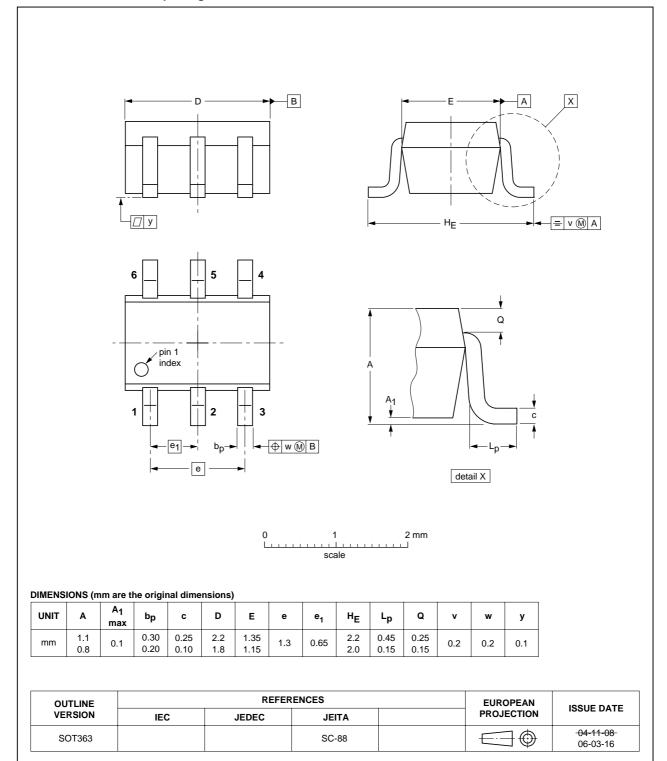


Fig 10. Package outline SOT363 (SC-88)

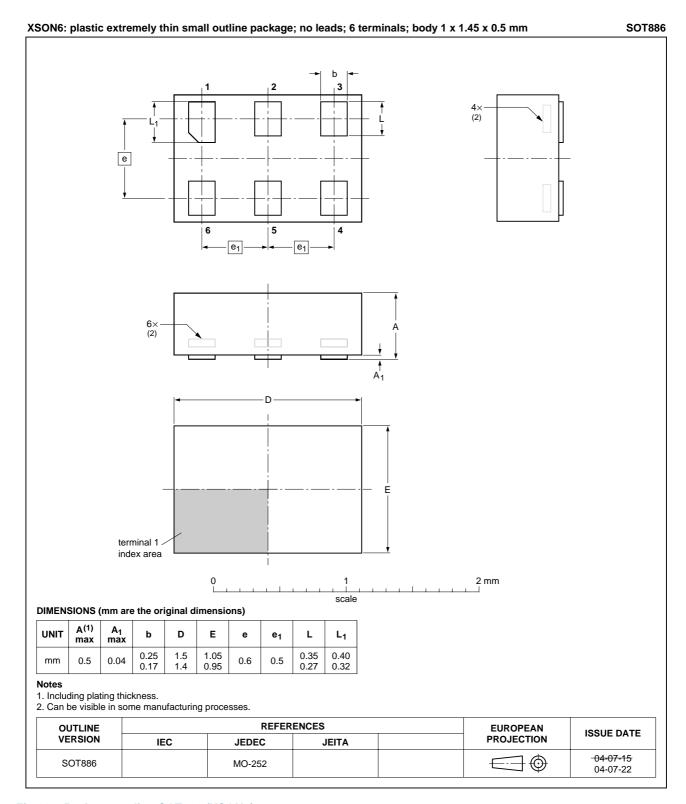


Fig 11. Package outline SOT886 (XSON6)

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15. Abbreviations

Table 18. Abbreviations

Acronym	Description
CDM	Charged Device Model
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model
MM	Machine Model

16. Revision history

Table 19. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AVC1T45_2	20090505	Product data sheet	-	74AVC1T45_1
Modifications:	 Conditions for 	or I _{CC} changed		
74AVC1T45_1	20080118	Product data sheet	-	-

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17. Legal information

17.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.

